

IN THE CLAIMS

Please amend the claims as follows:

1-3. (Canceled)

4. (Previously presented) A semiconductor device comprising:

an internal voltage supply circuit for generating an internal voltage from a power supply voltage;

an internal circuit which is operated by the internal voltage;

a switching transistor for receiving at a gate an operation signal output from the internal circuit; and

a load circuit which is connected to a drain of the switching transistor and consumes substantially the same amount of electric current as the amount of electric current which the internal circuit consumes during an operation period,

wherein by the operation signal, the switch transistor is turned OFF when the internal circuit is in an operation state and is turned ON when the internal circuit is in a non-operation state, and

the load circuit includes a first resistor and a load adjustment section connected in series to the first resistor.

5. (Currently amended) The semiconductor device of claim 4, wherein the amount of electric current which the first resistor and the load adjustment section consume is substantially the same as the amount of electric current which the internal circuit consumes during an the operation period.

6. (Original) The semiconductor device of claim 5, wherein the load adjustment section includes a second resistor and a fuse device connected in parallel to each other.

7. (Original) The semiconductor device of claim 5, wherein the load adjustment section includes a second resistor and a transistor connected in parallel to each other.

8. (Original) The semiconductor device of claim 7, further comprising a latch circuit connected to the transistor.

9. (Previously presented) The semiconductor device of claim 4, wherein the switching transistor is an n-channel transistor.

10. (Currently amended) The semiconductor device of claim 9, wherein the switching transistor has a source grounded and a the drain connected to the internal voltage supply circuit via the load circuit.

11. (Previously presented) The semiconductor device of claim 4, wherein the switching transistor is a p-channel transistor.

12. (Currently amended) The semiconductor device of claim 11, wherein the switching transistor has a source connected to the internal voltage supply circuit and a the drain grounded via the load circuit.

13. (Previously presented) An IC card comprising:
a semiconductor device which includes an internal voltage supply circuit for generating an internal voltage from a power supply voltage,

an internal circuit which is operated by the internal voltage,
a switching transistor for receiving at a gate an operation signal output from the internal circuit, and

a load circuit which is connected to a drain of the switching transistor and consumes substantially the same amount of electric current as the amount of electric current which the internal circuit consumes during an operation period and in which by the operation signal, the

switching transistor is turned OFF when the internal circuit is in an operation state and is turned ON when the internal circuit is in a non-operation state,

wherein the load circuit includes a first resistor and a load adjustment section connected in series to the first resistor.

14. (Cancelled)

15. (Currently amended) [[The]] A semiconductor device of claim 14 comprising:
an internal voltage supply circuit for generating an internal voltage from a power supply
voltage;

an internal circuit which is operated by the internal voltage;
a switching transistor for receiving at a gate an operation signal output from the internal
circuit; and

a load circuit which is connected to a drain of the switching transistor and consumes
substantially the same amount of electric current as the amount of electric current which the
internal circuit consumes during an operation period,

wherein by the operation signal, the switching transistor is turned OFF when the internal
circuit is in an operation state and is turned ON when the internal circuit is in a non-operation
state,

the load circuit includes a first resistor, and a load adjustment section for adjusting the
amount of electric current which the load circuit consumes when the switching transistor is
turned ON,

the load adjustment section includes a second resistor and a fuse device which are
connected in parallel to each other, and

if the amount of electric current which the first resistor consumes is more than the amount of electric current which the internal circuit consumes during [[an]] the operation period when the fuse device is not cut, [[and]] the amount of electric current which the load circuit consumes is adjusted to be substantially the same as the amount of electric current which the internal circuit consumes [[when]] by cutting the fuse device [[is cut]].